

L Number	Hits	Search Text	DB	Time stamp
1	19462	semiconductor and diode and cathode and anode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 10:02
2	2896	(semiconductor and diode and cathode and anode) and (trench or recess\$3 or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 10:03
3	1044	((semiconductor and diode and cathode and anode) and (trench or recess\$3 or groove)) and (dopant or impurity) and concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 10:04
4	65	((semiconductor and diode and cathode and anode) and (trench or recess\$3 or groove)) and (dopant or impurity) and concentration) and (pinch adj off)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 10:04
5	41	((((semiconductor and diode and cathode and anode) and (trench or recess\$3 or groove)) and (dopant or impurity) and concentration) and (pinch adj off)) and (reverse adj bias)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 10:05